

# 110V, 199A, 2.3mΩ N-channel Power SGT MOSFET

## JMSH1102TE

### Features

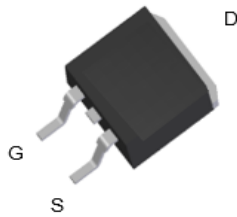
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- 100% UIS TESTED
- 100%  $\Delta V_{ds}$  TESTED
- Halogen-free; RoHS-compliant
- Pb-free plating

### Applications

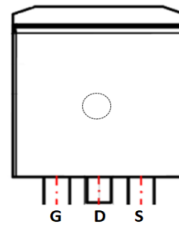
- Load Switch
- PWM Application
- Power Management

### Product Summary

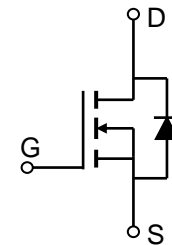
Parameters	Value	Unit
$V_{DSS}$	110	V
$V_{GS(th\_Typ)}$	3.0	V
$I_D(@V_{GS}=10V)$	199	A
$R_{DS(ON\_Typ)}(@V_{GS}=10V)$	2.3	mΩ



TO-263-3L Top View



Pin Assignment



Schematic Diagram

### Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH1102TE	SH1102T	3	Tape&Reel	TO-263-3L	800	4000

### Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-to-Source Voltage	110	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ\text{C}$	199
		$T_C = 100^\circ\text{C}$	126
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>	Refer to Fig.4	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(2)</sup>	1384	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	250
		$T_C = 100^\circ\text{C}$	100
$T_J, T_{STG}$	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(3)</sup>	32	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.5	

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	110	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 88\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.1	3.0	3.9	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance <sup>(4)</sup>	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	-	2.3	3.3	m $\Omega$
<b>Dynamic Characteristics</b>						
$R_g$	Gate Resistance	$f = 1\text{MHz}$	-	2.6	-	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 55\text{V},$ $f = 1\text{MHz}$	6778	9489	12810	pF
$C_{oss}$	Output Capacitance		1056	1479	1997	pF
$C_{rss}$	Reverse Transfer Capacitance		22	31	42	pF
$Q_g$	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 55\text{V}, I_D = 20\text{A}$	95	133	179	nC
$Q_{gs}$	Gate Source Charge		33	46	63	nC
$Q_{gd}$	Gate Drain ("Miller") Charge		19	27	36	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}, V_{DD} = 55\text{V}$ $I_D = 20\text{A}, R_{GEN} = 6.2\Omega$	-	40	-	ns
$t_r$	Turn-On Rise Time		-	59	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	110	-	ns
$t_f$	Turn-Off Fall Time		-	64	-	ns
<b>Body Diode Characteristics</b>						
$I_S$	Maximum Continuous Body Diode Forward Current		-	-	199	A
$I_{SM}$	Maximum Pulsed Body Diode Forward Current		-	-	796	A
$V_{SD}$	Body Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 20\text{A}$	-		1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$	68	95	129	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	306	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2.  $E_{AS}$  condition: Starting  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = 55\text{V}$ ,  $V_G = 10\text{V}$ ,  $R_G = 25\text{ohm}$ ,  $L = 3\text{mH}$ ,  $I_{AS} = 30.38\text{A}$ ,  $V_{DD} = 0\text{V}$  during time in avalanche.
  3.  $R_{\theta JA}$  is measured with the device mounted on a  $1\text{inch}^2$  pad of 2oz copper FR4 PCB.
  4. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$ .



## Typical Performance Characteristics

Figure 1: Power De-rating



Figure 2: Current De-rating

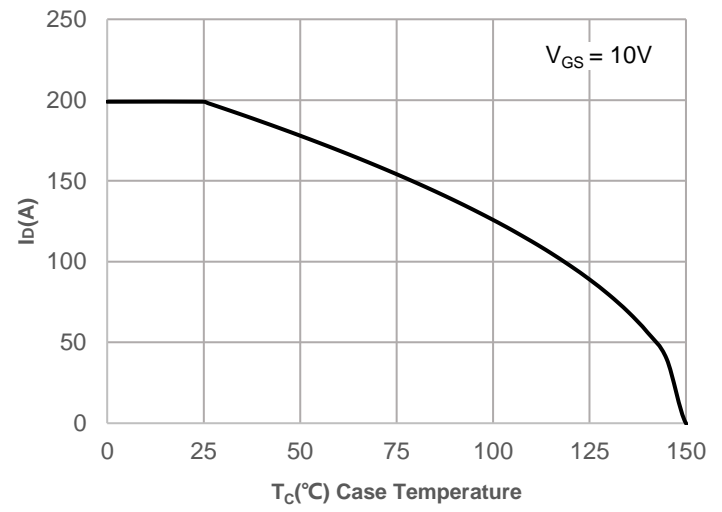


Figure 3: Normalized Maximum Transient Thermal Impedance

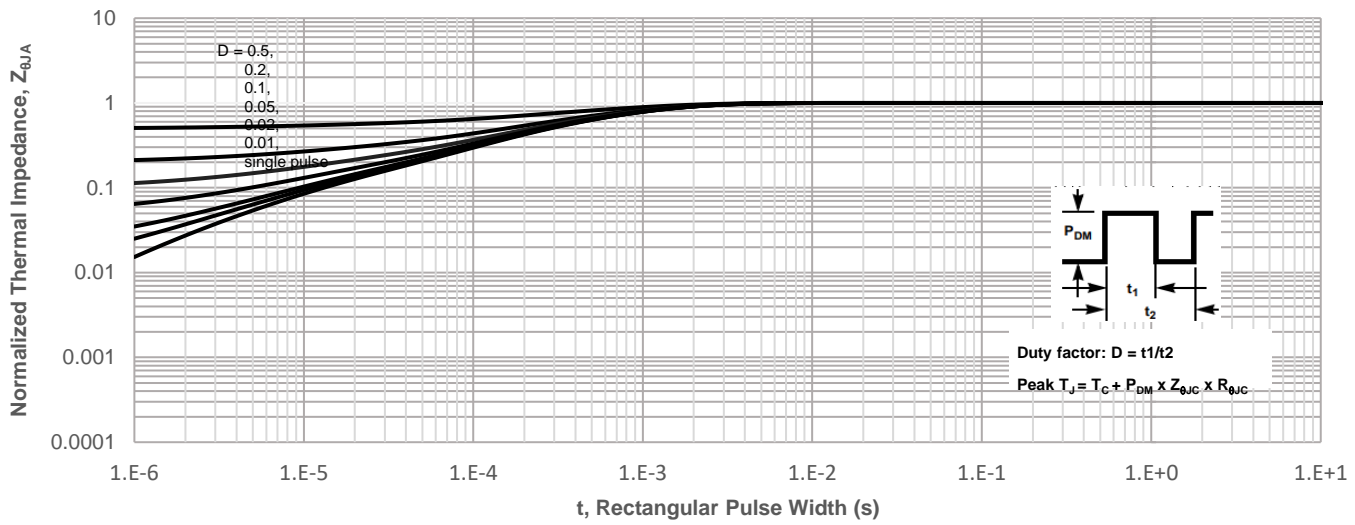
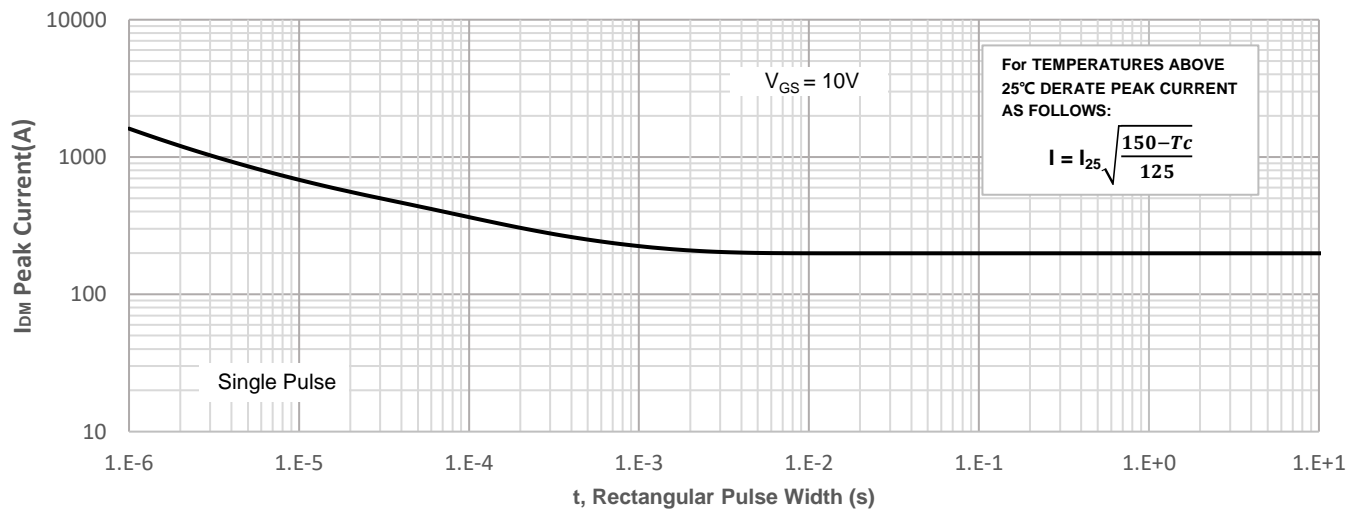
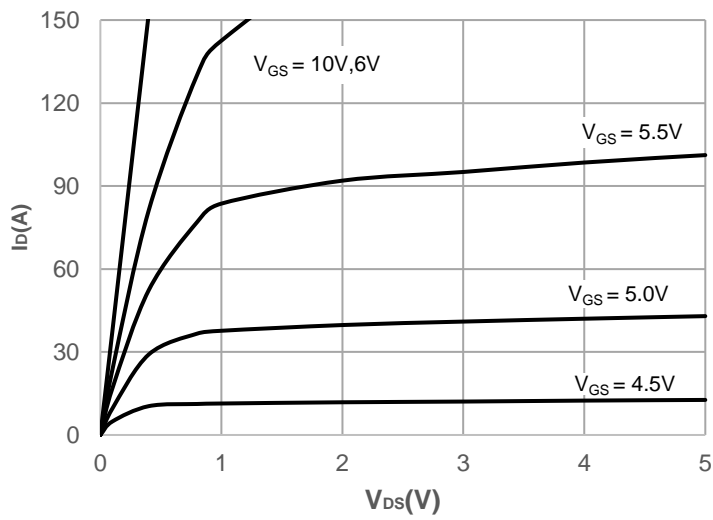
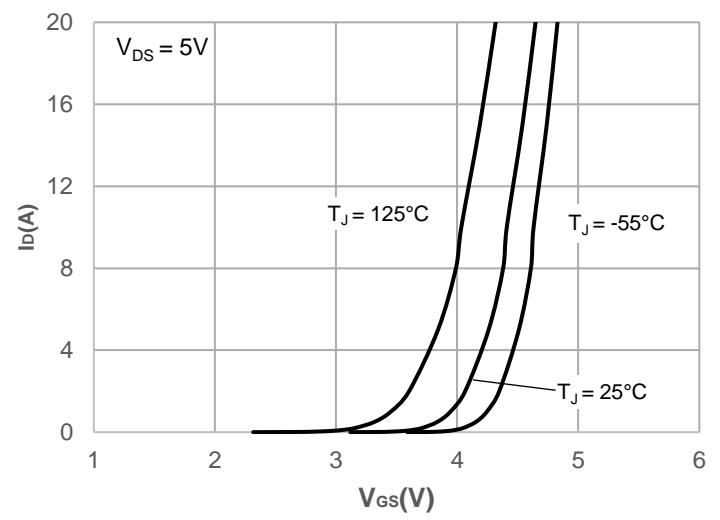
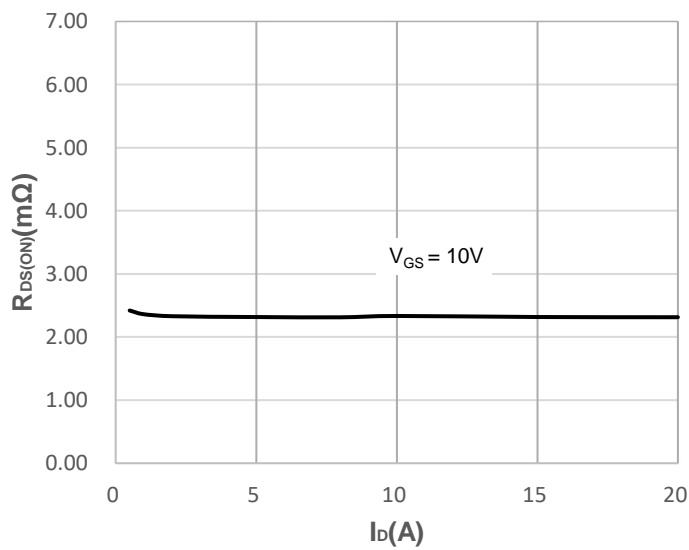
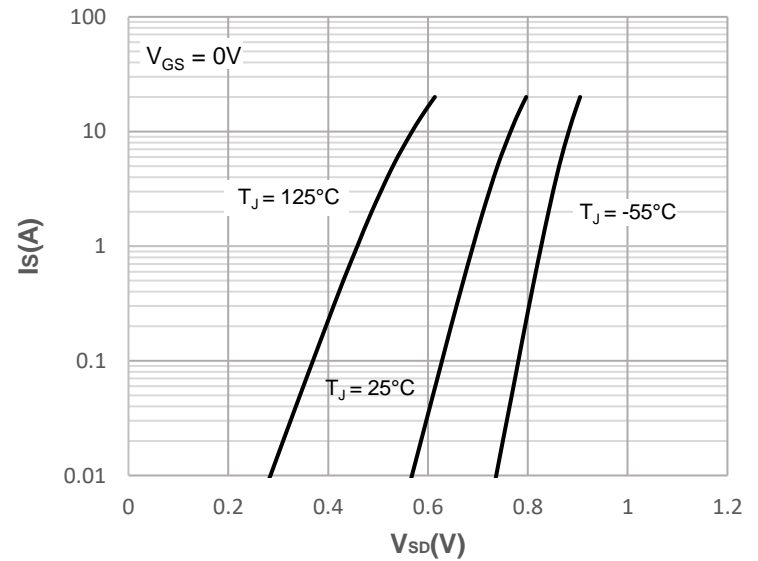
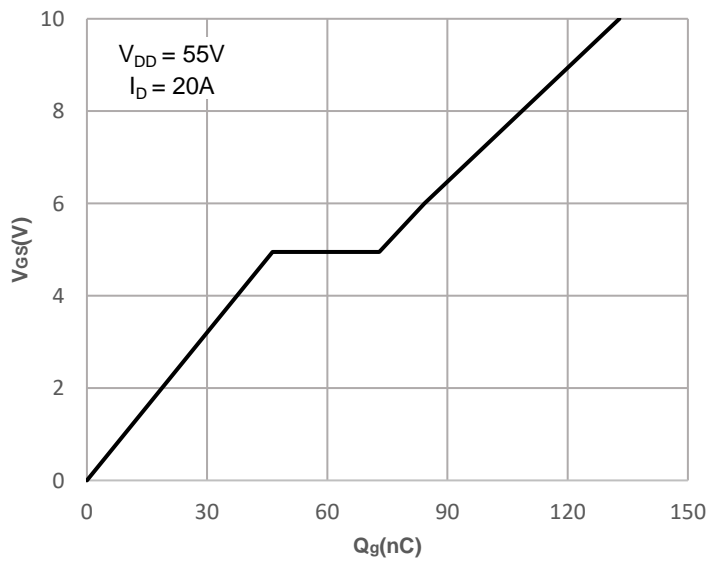
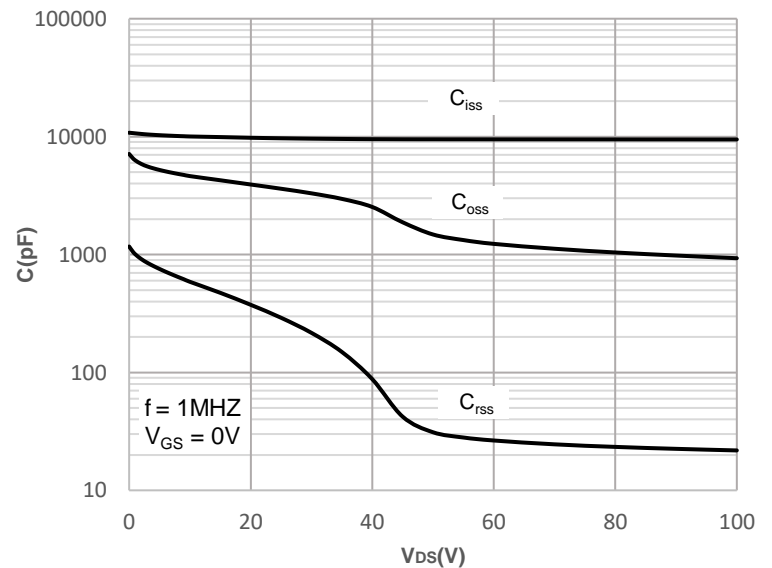


Figure 4: Peak Current Capacity



## Typical Performance Characteristics

**Figure 5: Output Characteristics**

**Figure 6: Typical Transfer Characteristics**

**Figure 7: On-resistance vs. Drain Current**

**Figure 8: Body Diode Characteristics**

**Figure 9: Gate Charge Characteristics**

**Figure 10: Capacitance Characteristics**


## Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

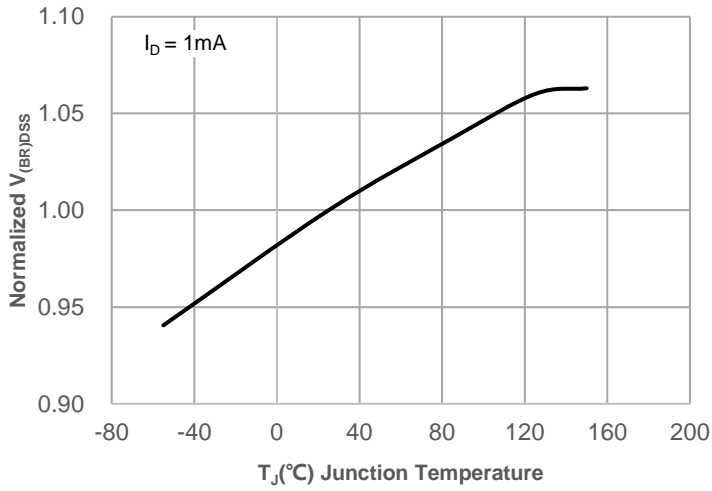


Figure 12: Normalized on Resistance vs. Junction Temperature

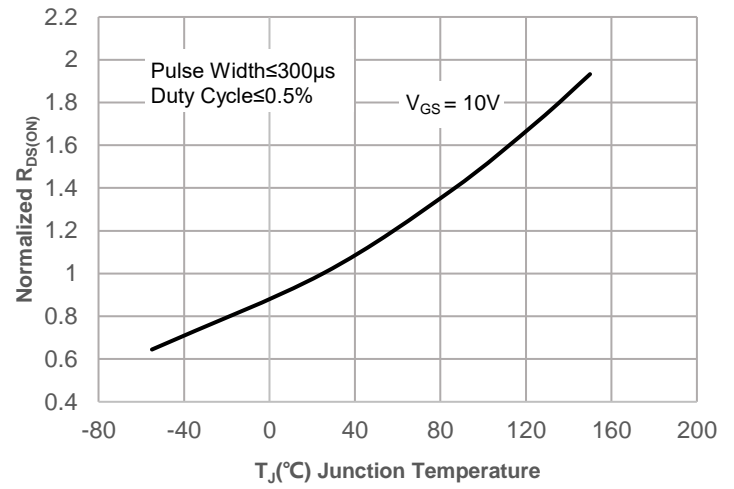


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

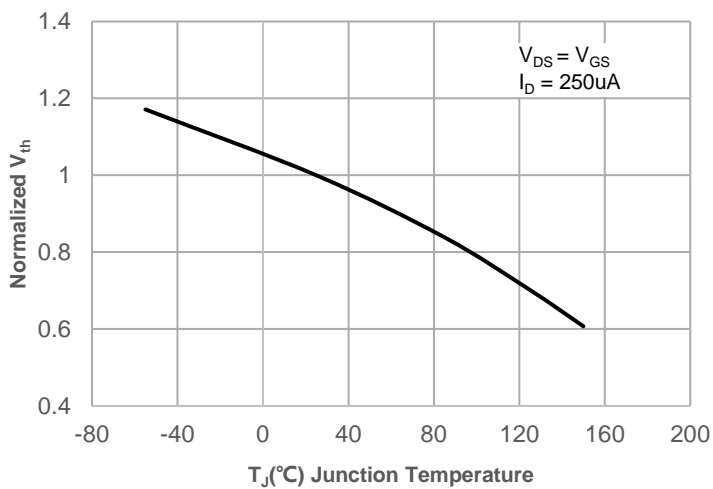


Figure 14:  $R_{DS(ON)}$  vs.  $V_{GS}$

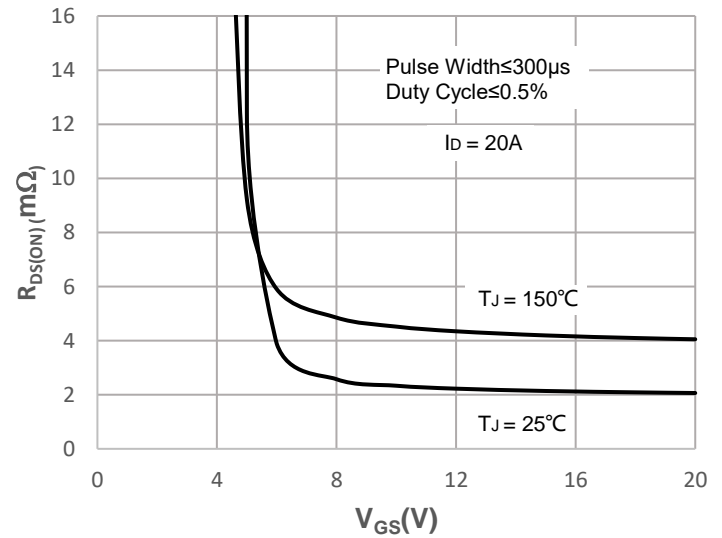
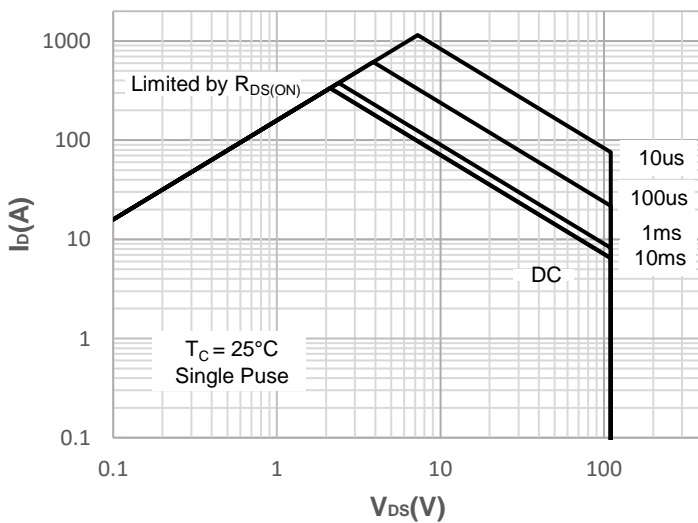


Figure 15: Maximum Safe Operating Area



### Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

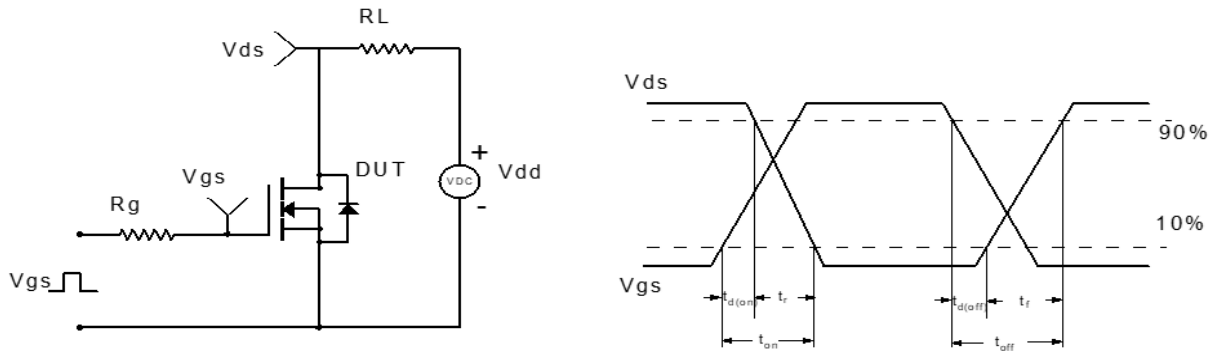


Figure 2: Resistive Switching Test Circuit & Waveform

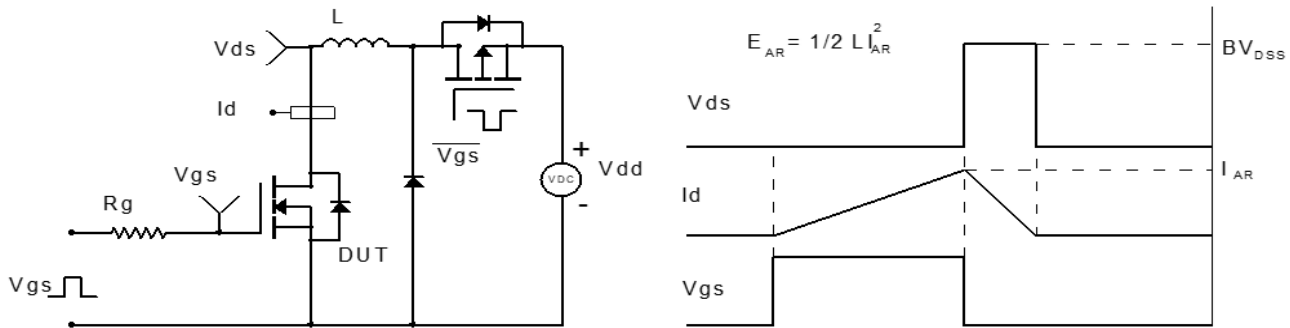


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

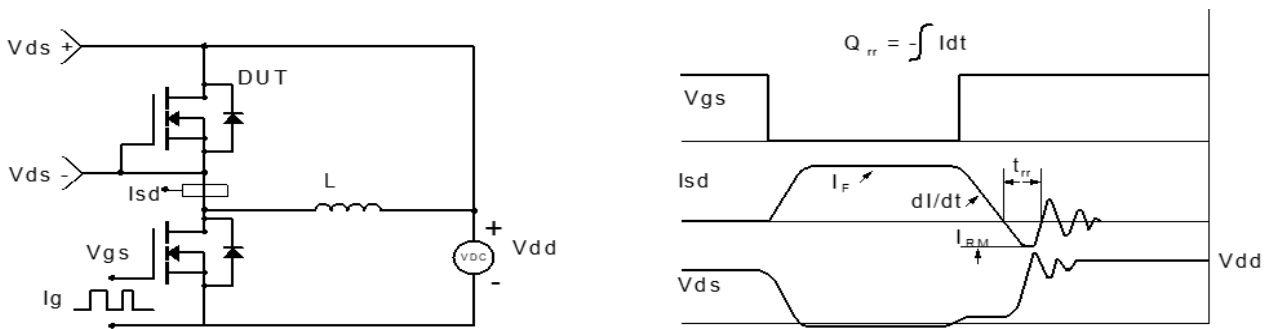
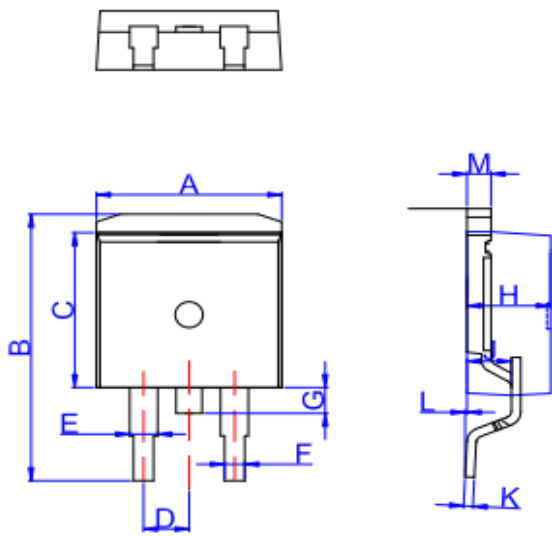
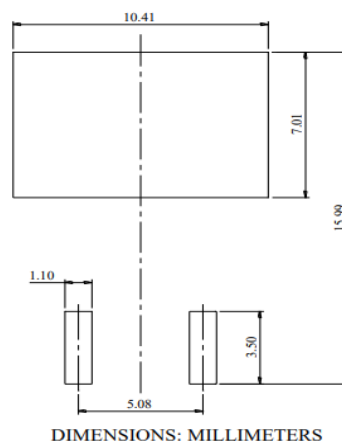


Figure 4: Diode Recovery Test Circuit & Waveform



**Package Mechanical Data(TO-263-3L)**

**TO-263**
**Recommended Footprint**

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053



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